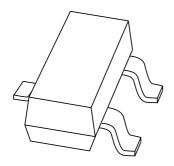
## DISCRETE SEMICONDUCTORS

# DATA SHEET



## BAV199 Low-leakage double diode

Product data sheet Supersedes data of 1999 May 11 2001 Oct 12



## Low-leakage double diode

**BAV199** 

#### **FEATURES**

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

#### **APPLICATION**

 Low-leakage current applications in surface mounted circuits.

#### **DESCRIPTION**

Epitaxial, medium-speed switching, double diode in a small SOT23 plastic SMD package. The diodes are connected in series.

#### **MARKING**

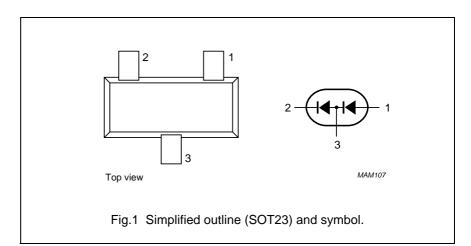
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BAV199	JY*

#### Note

\* = p: Made in Hong Kong.
 \* = t: Made in Malaysia.
 \* = W: Made in China.

#### **PINNING**

PIN	DESCRIPTION
1	anode
2	cathode
3	anode; cathode



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode			•	•	
$V_{RRM}$	repetitive peak reverse voltage		_	85	V
V <sub>R</sub>	continuous reverse voltage		_	75	V
I <sub>F</sub>	continuous forward current	single diode loaded; note 1; see Fig.2	_	160	mA
		double diode loaded; note 1; see Fig.2	_	140	mA
I <sub>FRM</sub>	repetitive peak forward current		_	500	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; $T_j = 25$ °C prior to surge; see Fig.4			
		$t_p = 1 \mu s$	_	4	Α
		$t_p = 1 \text{ ms}$	_	1	Α
		$t_p = 1 \text{ s}$	_	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C

#### Note

1. Device mounted on a FR4 printed-circuit board.

## Low-leakage double diode

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#### **ELECTRICAL CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V <sub>F</sub>	forward voltage	see Fig.3			
		I <sub>F</sub> = 1 mA	_	900	mV
		I <sub>F</sub> = 10 mA	_	1000	mV
		I <sub>F</sub> = 50 mA	_	1100	mV
		I <sub>F</sub> = 150 mA	_	1250	mV
I <sub>R</sub>	reverse current	see Fig.5			
		V <sub>R</sub> = 75 V	0.003	5	nA
		V <sub>R</sub> = 75 V; T <sub>j</sub> = 150 °C	3	80	nA
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0; see Fig.6	2	_	pF
t <sub>rr</sub>	reverse recovery time	when switched from I <sub>F</sub> = 10 mA to	0.8	3	μs
		$I_R$ = 10 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.7			

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point		360	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

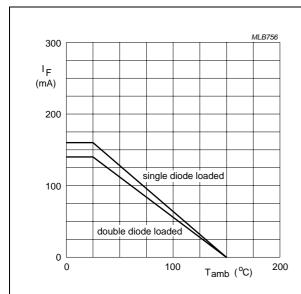
#### Note

1. Device mounted on a FR4 printed-circuit board.

## Low-leakage double diode

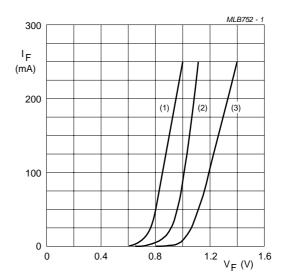
**BAV199** 

#### **GRAPHICAL DATA**



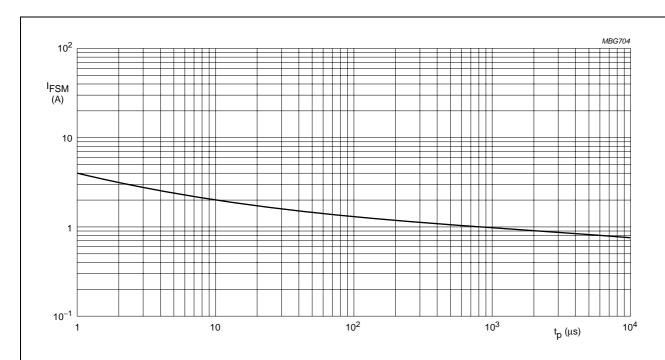
Device mounted on a FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1)  $T_j = 150$  °C; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage; per diode.

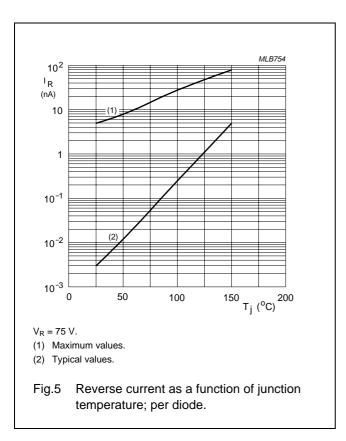


Based on square wave currents;  $T_i = 25$  °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

## Low-leakage double diode

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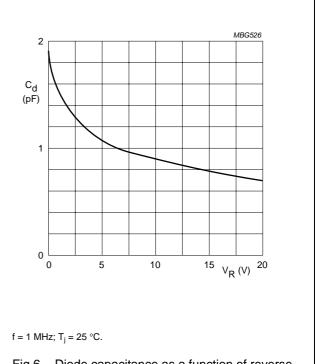
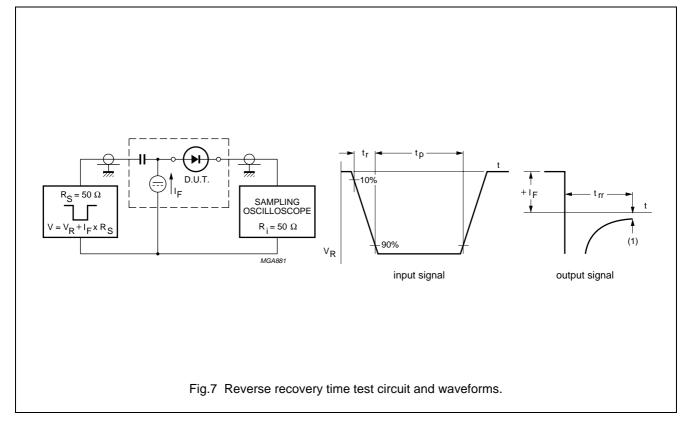


Fig.6 Diode capacitance as a function of reverse voltage; per diode; typical values.



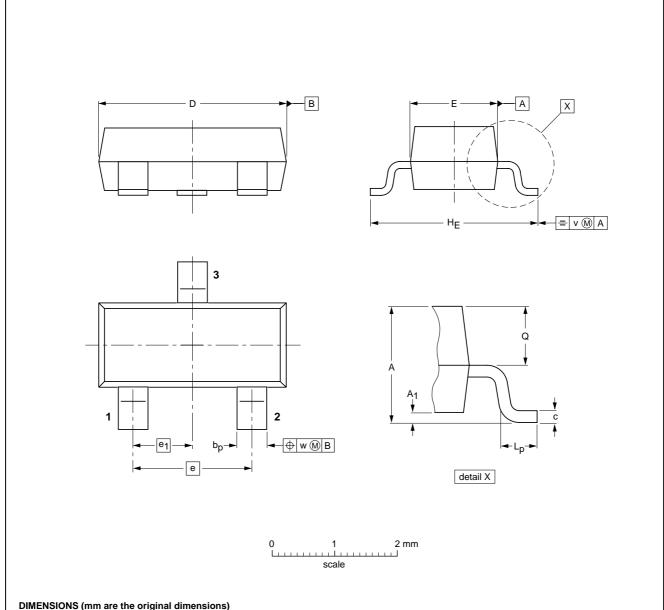
## Low-leakage double diode

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the	e original dimensions)
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UNIT	A	A <sub>1</sub> max.	bp	С	D	E	е	e <sub>1</sub>	HE	L <sub>p</sub>	Q	٧	w	
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE	
SOT23		TO-236AB				<del>97-02-28</del> 99-09-13	

2001 Oct 12 6

### Low-leakage double diode

**BAV199** 

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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